

SOT-23 Plastic-Encapsulate Diodes

Switching Diode

Features:

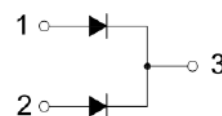
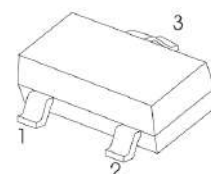
- Low Leakage Current
- High Switching Speed

Application:

- Low-leakage Current Applications
in Surface Mounted Circuits

MARKING:JX

SOT-23



MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	85	V
V_R	DC Blocking Voltage	75	V
I_F	Forward Current(single diode)	215	mA
	Forward Current(double diode)	125	
I_{FRM}	Repetitive Peak Forward Current	500	mA
I_{FSM}	Non-repetitive Peak Forward Current@ $t_p=1\mu\text{A}$	4	A
P_D	Power Dissipation	250	mW
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	500	$^{\circ}\text{C}/\text{W}$
T_j	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55~+150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS($T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Reverse voltage	$V_{(BR)}$	$I_R=100\mu\text{A}$	75			V
Reverse current	I_R	$V_R=75\text{V}$			5	nA
Forward voltage	V_F	$I_F=1\text{mA}$			0.9	V
		$I_F=10\text{mA}$			1	
		$I_F=50\text{mA}$			1.1	
		$I_F=150\text{mA}$			1.25	
Total capacitance	C_{tot}	$V_R=0, f=1\text{MHz}$		2		pF
Reverse recovery time	t_{rr}	$I_F=I_R=10\text{mA}, I_{rr}=0.1 \times I_R, R_L=100\Omega$			3	μs